

ABSTRACT OF THE DISCLOSURE

Strip-shaped alignment marks 14 are juxtaposed with each other in a silicon oxide film 12 formed on a silicon wafer 10. Each alignment mark 14 comprises a plurality of grooves 16 formed side by side in the silicon oxide film 12. An amorphous silicon film 18 is buried in the grooves 16. Thus, the alignment marks 14 are formed in a thus-formed line-and-space pattern. Accordingly, waveforms of detected signals having high contrast and little deformation can be obtained, and alignment of wafers with high accuracy can be realized.